



HLJ Technology Co., Ltd.

# Preliminary Specification

Project Code : 3H501

Product : 1135nm 32mil-552E

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## Specification

The specification applies to GaAs infrared chip for 1135nm wavelength range.

The 3H501 is a 1135nm 32 mil Vertical Cavity Surface Emitting Laser (VCSEL) chip. The product characterized by the visible light wavelength and unique oxide-confined process of VCSELs.

### Features

- Wavelength: 1135nm
- Chip size:  $800 \times 800 \pm 15 \mu\text{m}$
- Chip thickness :  $150 \pm 15 \mu\text{m}$
- Drive current : 5A
- Output power : 2.6W @ pulse width 20 $\mu\text{s}$ , Duty 6%
- Electrode side : Gold alloy on both anode P(emission side) and cathode N(backside)
- Other configurations available on request

### Applications

- Moving sensor/ Gesture
- Optical encoders
- 3D sensing
- Health or medical product
- Mobile and consumer

### Electrical Optical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Threshold Current	$I_{th}$	-	400	-	mA	
Output Power	$P_o$	-	2600	-	mW	$I_f=5\text{A}$
Forward Voltage	$V_f$	1.7	2.0	2.3	V	$I_f=5\text{A}$
Slope Efficiency (S.E.)	$\eta_s$	0.3	0.4	-	W/A	$I_f=5\text{A}$
Center Wavelength	$\lambda_c$	1125	1135	1145	nm	$I_f=5\text{A}$
Power Conversion Efficiency	PCE	20		-	%	$I_f=5\text{A}$
Wavelength Shift	$\Delta\lambda/\Delta T$	-	0.07	-	nm/ $^\circ\text{C}$	$I_f=5\text{A}$
Beam Divergence	$\theta$	-	24	-	deg.	Full Width 1/ $e^2$

Note 1: Forward Voltage ( $V_f$ ) measurement allowance is  $\pm 0.1\text{V}$ .

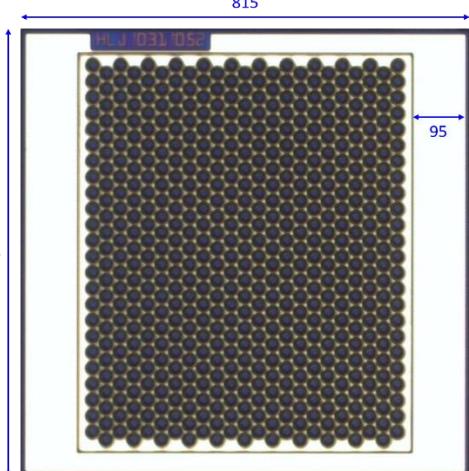
Note 2: Center Wavelength ( $\lambda_c$ ) measurement allowance is  $\pm 1.5\text{nm}$ .

Note 3: Others measurement allowance is  $\pm 10\%$ .

Note 4: Wafer on probe system test and chip mounted on Cu star board, and measured with operating bias current @ 5A, Pulse Width:20 $\mu\text{s}$ , Duty Cycle 6%.



## Dimensions



Specification	Min.	Typ.	Max.
Chip width	800	815	830
Chip length	800	815	830
Chip thickness	135	150	165
Bond pad width	-	95	-

Unit: µm

## Other Information

### ■ RoHs Compliance:

HLJ committed to environment protection and sustainable development, this part complies with EU 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) and the relevant of held as part of our controlled documentation.

### ■ Packaging Q'ty:

500 ea/ die sheet, 8 die sheet/pack, 6 pack/ box, 6 box/ cargo box

### ■ ESD Protection:

VCSEL is very sensitive to Electrostatic discharge (ESD) and Electrical over stress (EOS), excessive ESD have damage the chip and result in performance degradation. Make sure during the whole usage and installation process that no ESD exist and electrical circuits are equipped with surge protection.

### ■ Important Notice:

The data provided in this data sheet shall be typical. In accordance with the HLJ policy of continuous improvement, specifications may change without notice.

## Revision History

Revision	Description	Author	Release Date
0.1	Establish a Datasheet	Yi-Fang, Chen	2023/3/24